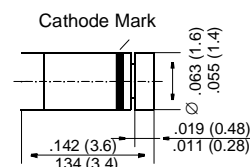


## LL4148

### FEATURES

- Silicon Epitaxial Planar Diode
- Fast switching diode
- This diode is also available in other case styles including: the DO-35 case with the type designation 1N4148, the SOD-23 case with the type designation 1N4148W, and the SOT-23 case with the type designation

### MiniMELE



### MECHANICAL DATA

- Case: MiniMELF
- Weight: approx: 0.05gram

*Dimensions in inches and (millimeters)*

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

- Ratings at 25°C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Reverse Voltage	$V_R$	75	V
Peak Reverse Voltage	$V_{RM}$	100	V
Forward DC current at $T_{amb} = 25\text{ }^\circ\text{C}$	$I_F$	200 <sup>1)</sup>	mA
Rectified Current (Average) Half Wave Rectification with Resist. Load at $T_{amb} = 25\text{ }^\circ\text{C}$ and $f \geq 50\text{ Hz}$	$I_0$	150 <sup>1)</sup>	mA
Surge Forward Current at $t < 1\text{ s}$ and $T_j = 25\text{ }^\circ\text{C}$	$I_{FSM}$	500	mA
Power Dissipation at $T_{amb} = 25\text{ }^\circ\text{C}$	$P_{tot}$	500 <sup>1)</sup>	mW
Junction Temperature	$T_j$	175	°C
Storage Temperature Range	$T_S$	-65 to +175	°C

<sup>1)</sup> Valid provided that electrodes are kept at ambient temperature.

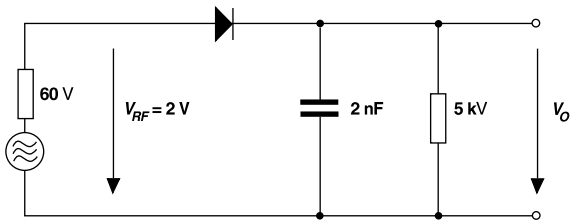


## ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 10 \text{ mA}$	$V_F$	–	–	1	V
Leakage Current at $V_R = 20 \text{ V}$ at $V_R = 75 \text{ V}$ at $V_R = 20 \text{ V}, T_j = 150 \text{ °C}$	$I_R$ $I_R$ $I_R$	– – –	– – –	25 5 50	nA $\mu\text{A}$ $\mu\text{A}$
Capacitance at $V_F = V_R = 0$	$C_{\text{tot}}$	–	–	4	pF
Voltage Rise when Switching ON tested with 50 mA Forward Pulses $t_p = 0.1 \mu\text{s}$ , Rise Time < 30 ns, $f_p = 5$ to 100 kHz	$V_{\text{fr}}$	–	–	2.5	V
Reverse Recovery Time from $I_F = 10 \text{ mA}$ to $I_R = 1 \text{ mA}$ , $V_R = 6 \text{ V}$ , $R_L = 100 \Omega$	$t_{\text{rr}}$	–	–	4	ns
Thermal Resistance Junction to Ambient Air	$R_{\text{thJA}}$	–	–	0.35 <sup>1)</sup>	K/mW
Rectification Efficiency at $f = 100 \text{ MHz}$ , $V_{\text{RF}} = 2 \text{ V}$	$\eta_v$	0.45	–	–	–

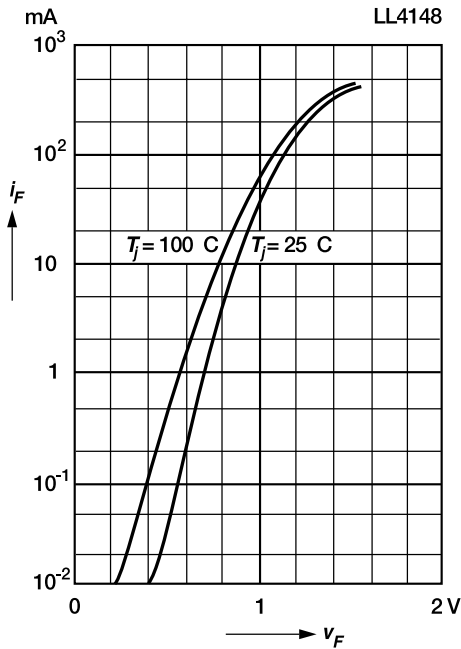
<sup>1)</sup> Valid provided that electrodes are kept at ambient temperature.



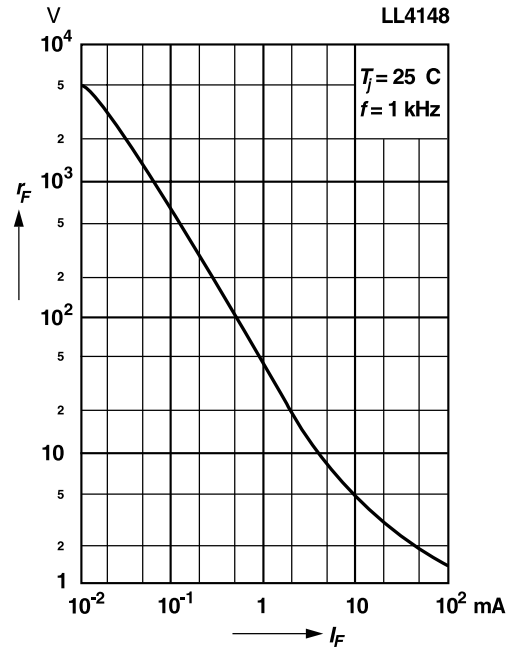
**Rectification Efficiency Measurement Circuit**

## RATINGS AND CHARACTERISTIC CURVES LL4148

Forward characteristics

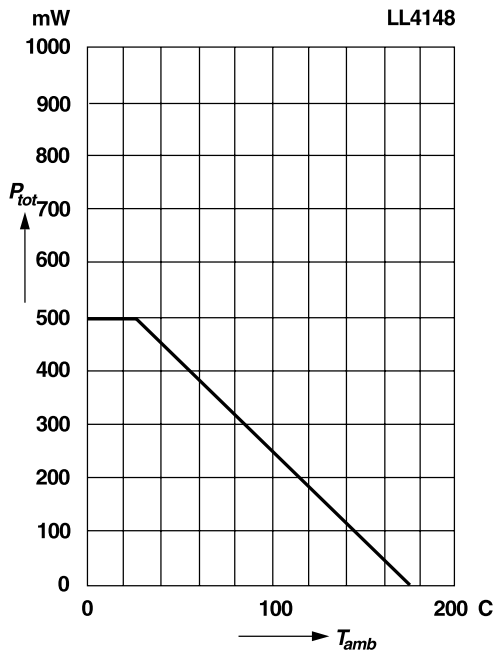


Dynamic forward resistance versus forward current

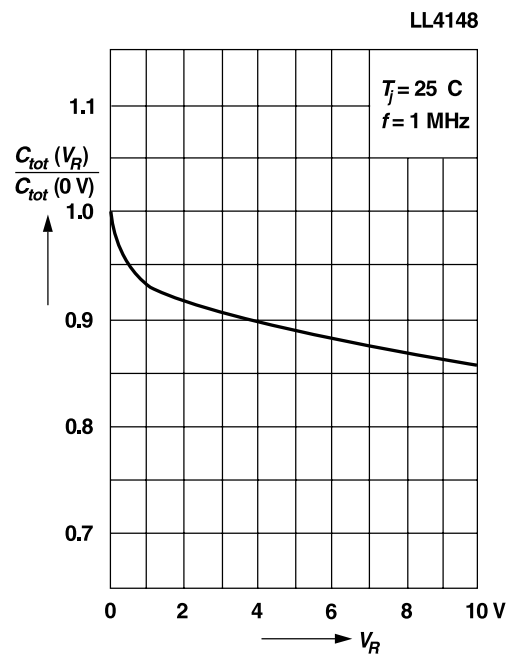


Admissible power dissipation versus ambient temperature

Valid provided that electrodes are kept at ambient temperature

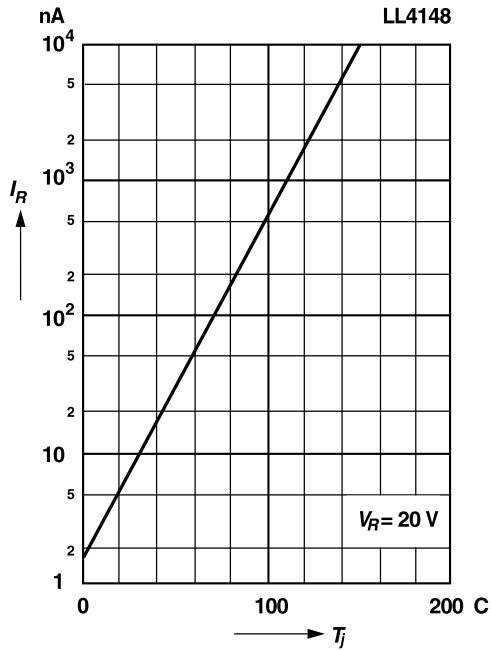


Relative capacitance versus reverse voltage



## RATINGS AND CHARACTERISTIC CURVES LL4148

Leakage current  
versus junction temperature



Admissible repetitive peak forward current versus pulse duration

Valid provided that electrodes are kept at ambient temperature

